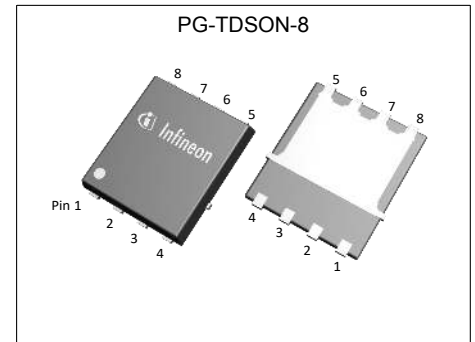


# MOSFET

## OptiMOS™5 Power-Transistor, 80 V

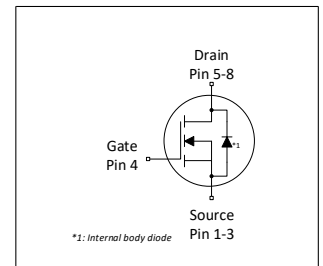
### Features

- Optimized for Synchronous Rectification in server and desktop
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	80	V
$R_{DS(on),max}$	2.6	m $\Omega$
$I_D$	184	A
$Q_{oss}$	88	nC
$Q_G(0V..10V)$	74	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSC026N08NS5	PG-TDSON-8	026N08NS	-

<sup>1)</sup> J-STD20 and JESD22

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	184 116 23	A	$V_{GS}=10\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=50\text{K/W}^2)$
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	-	-	736	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse <sup>4)</sup>	$E_{AS}$	-	-	370	mJ	$I_D=50\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	156 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$ , $R_{thJA}=50\text{ K/W}^2)$
Operating and storage temperature	$T_j$ , $T_{stg}$	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case, bottom	$R_{thJC}$	-	0.5	0.8	K/W	-
Thermal resistance, junction - case, top	$R_{thJC}$	-	-	20	K/W	-
Device on PCB, 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	50	K/W	-

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	$V_{DS}=V_{GS}$ , $I_D=115\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	10	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	2.2 3.0	2.6 3.9	$\text{m}\Omega$	$V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=25\text{ A}$
Gate resistance	$R_G$	-	1.9	2.9	$\Omega$	-
Transconductance	$g_{fs}$	60	120	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=50\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	5200	6800	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>1)</sup>	$C_{oss}$	-	840	1100	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>1)</sup>	$C_{rss}$	-	38	66	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	18	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ , $R_{G,ext}=3\text{ }\Omega$
Rise time	$t_r$	-	14	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ , $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	47	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ , $R_{G,ext}=3\text{ }\Omega$
Fall time	$t_f$	-	16	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=50\text{ A}$ , $R_{G,ext}=3\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	24	-	nC	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	14	-	nC	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge <sup>1)</sup>	$Q_{gd}$	-	16	23	nC	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	25	-	nC	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	74	92	nC	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.5	-	V	$V_{DD}=40\text{ V}$ , $I_D=50\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	64	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge <sup>1)</sup>	$Q_{oss}$	-	88	117	nC	$V_{DD}=40\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	118	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	736	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.85	1.1	V	$V_{GS}=0\text{ V}, I_F=50\text{ A}, T_j=25\text{ °C}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	56	112	ns	$V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	92	184	nC	$V_R=40\text{ V}, I_F=50\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test.

### 4 Electrical characteristics diagrams

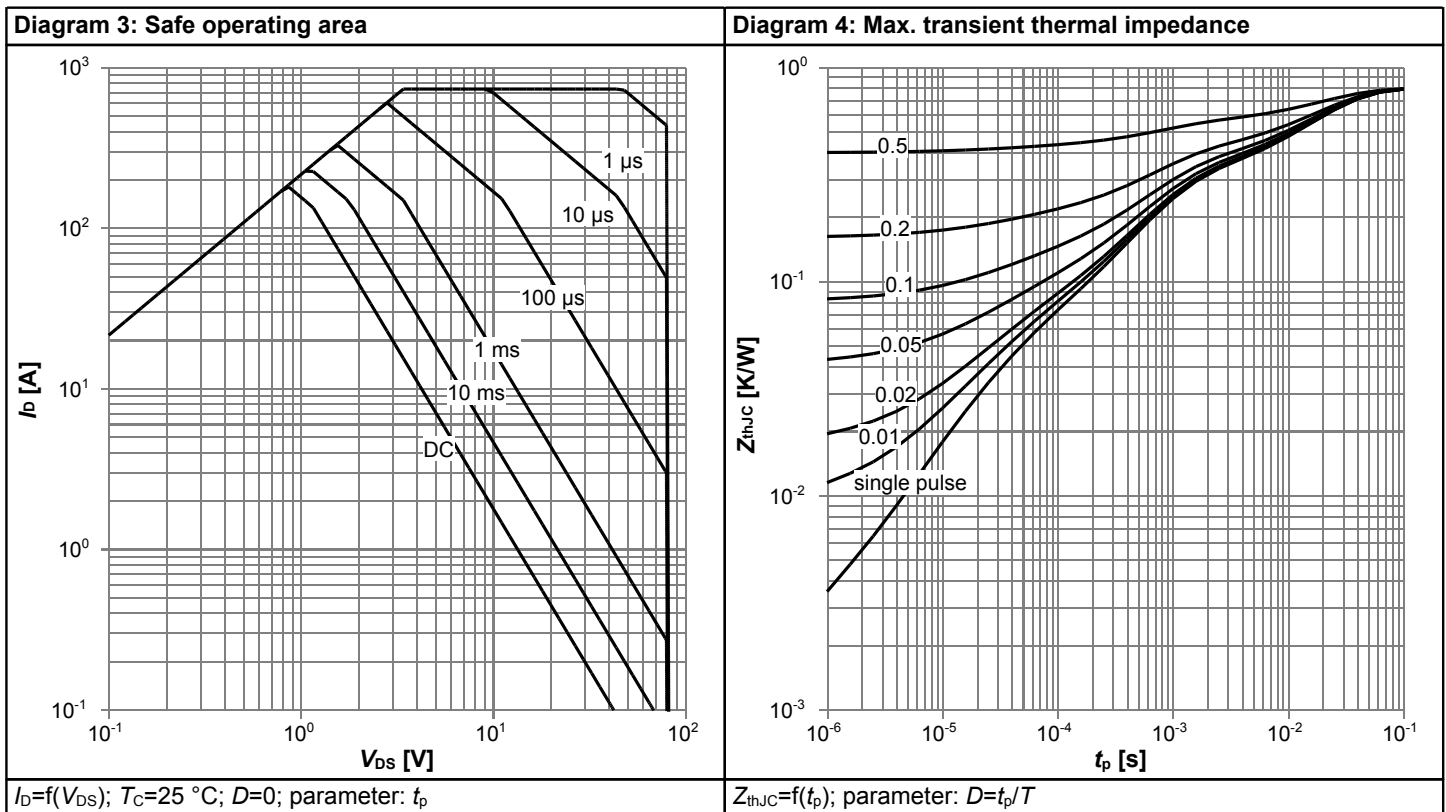
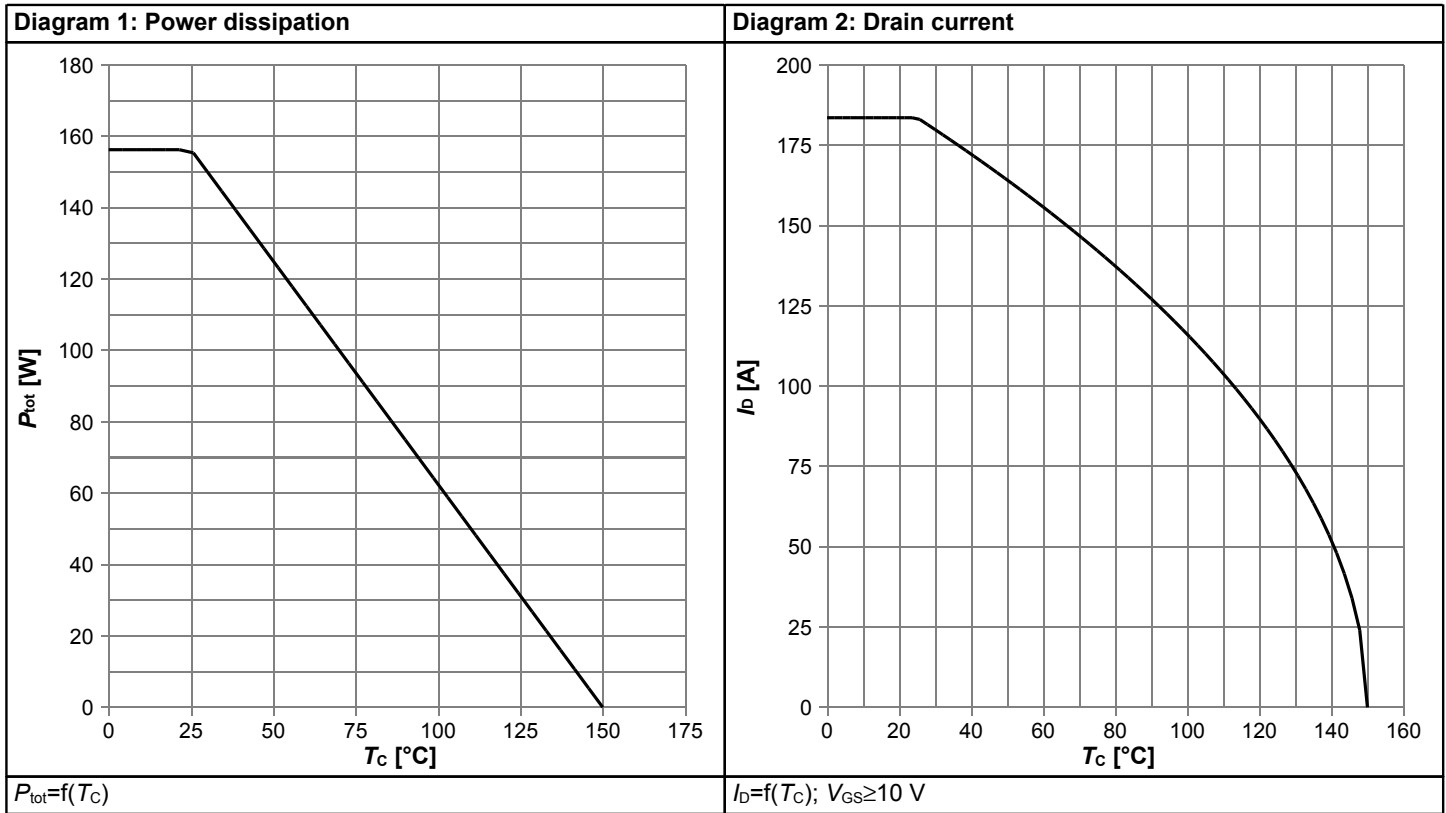
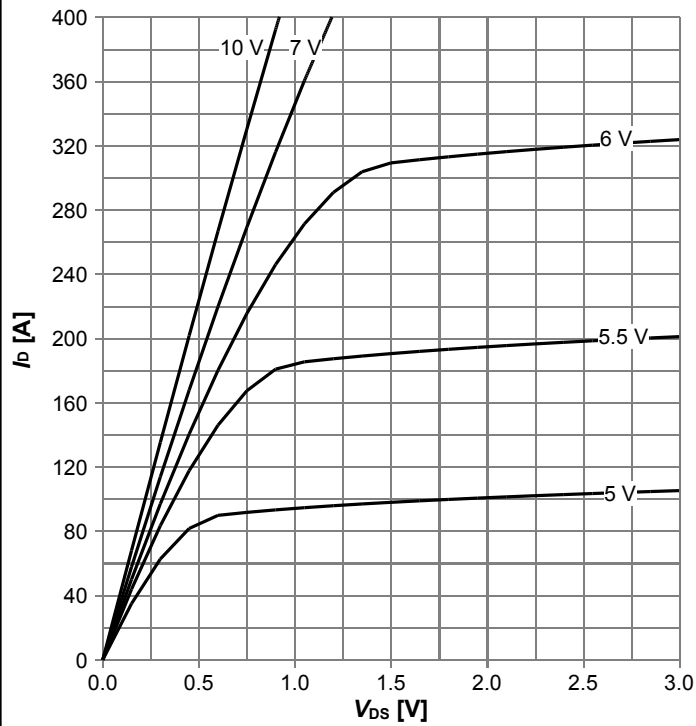
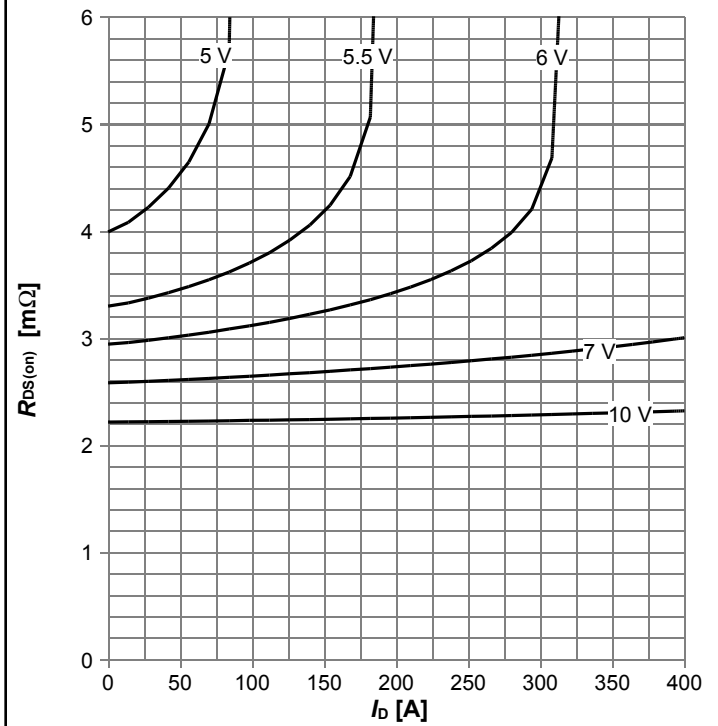


Diagram 5: Typ. output characteristics



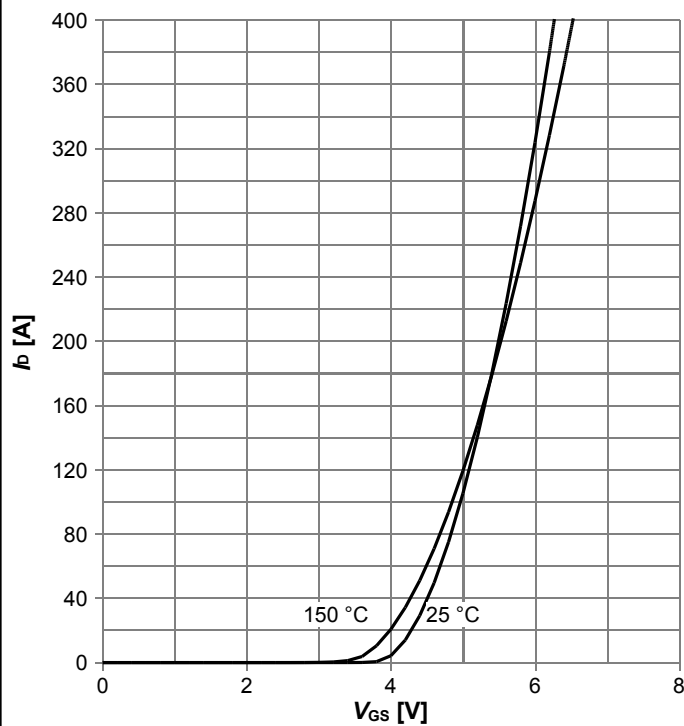
$I_D = f(V_{DS}); T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



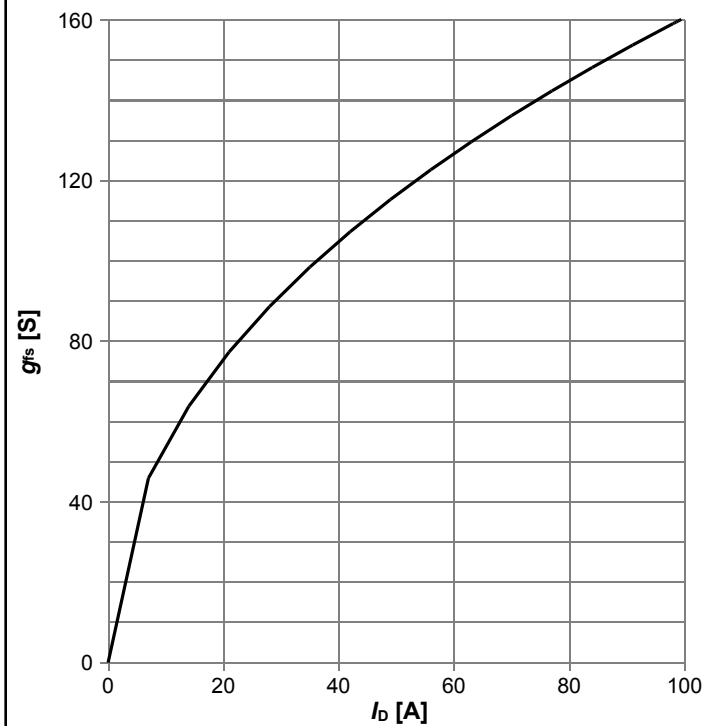
$R_{DS(on)} = f(I_D); T_j = 25\text{ °C};$  parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



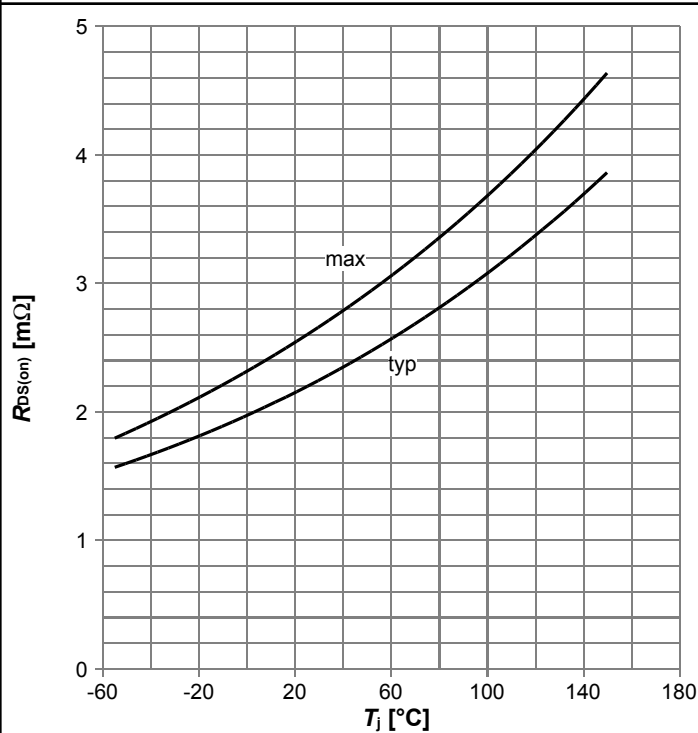
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max};$  parameter:  $T_j$

Diagram 8: Typ. forward transconductance



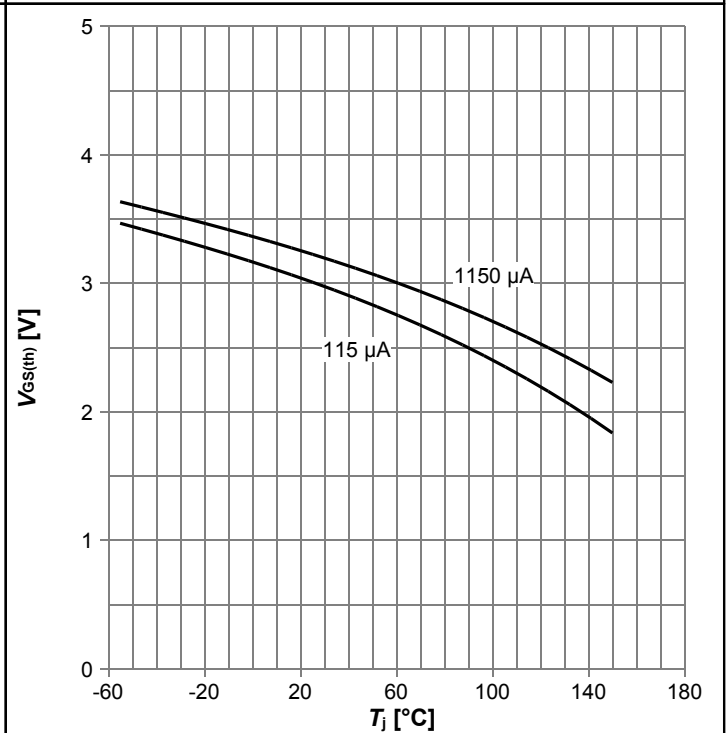
$g_{fs} = f(I_D); T_j = 25\text{ °C}$

Diagram 9: Drain-source on-state resistance



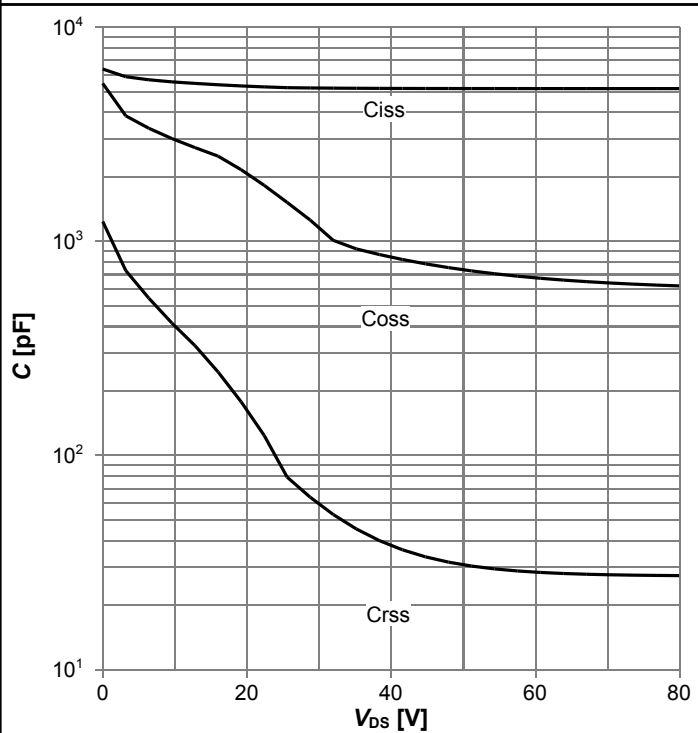
$R_{DS(on)}=f(T_j)$ ;  $I_D=50$  A;  $V_{GS}=10$  V

Diagram 10: Typ. gate threshold voltage



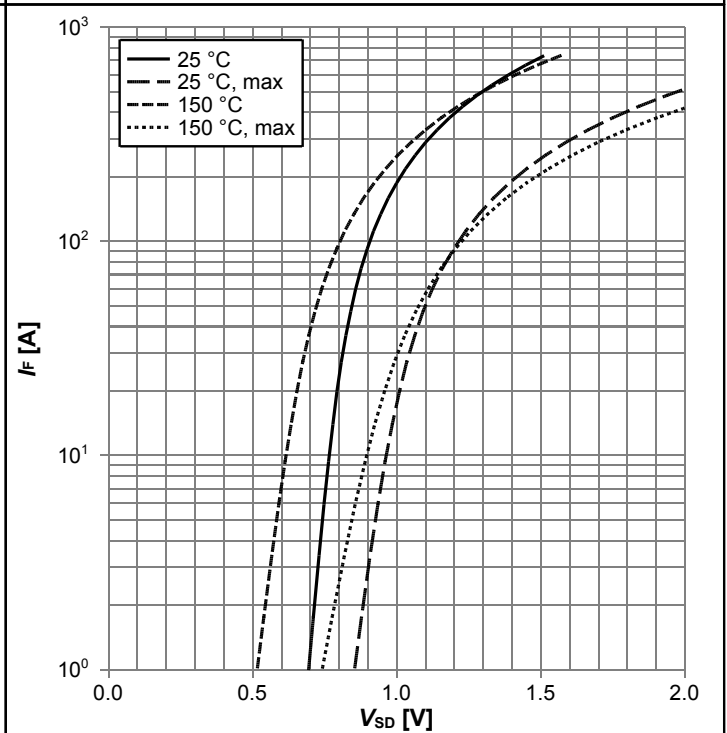
$V_{GS(th)}=f(T_j)$ ;  $V_{GS}=V_{DS}$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

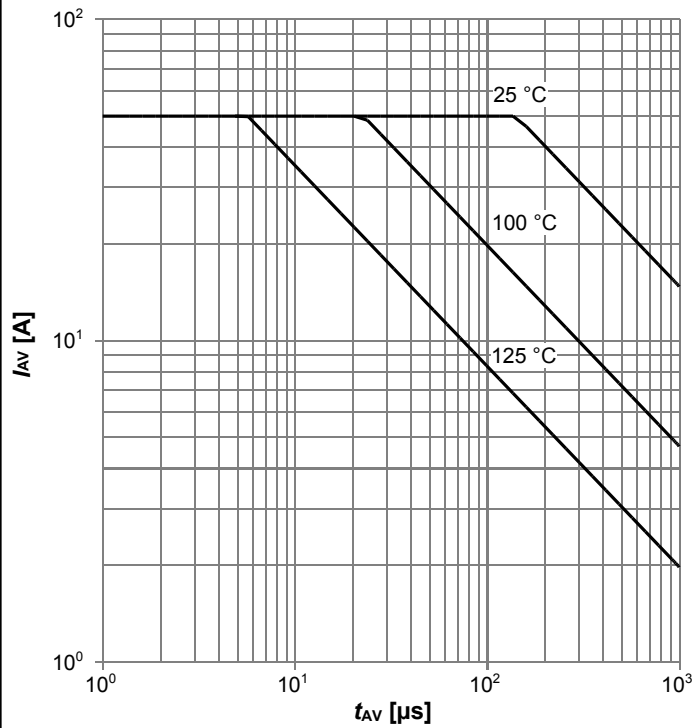
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

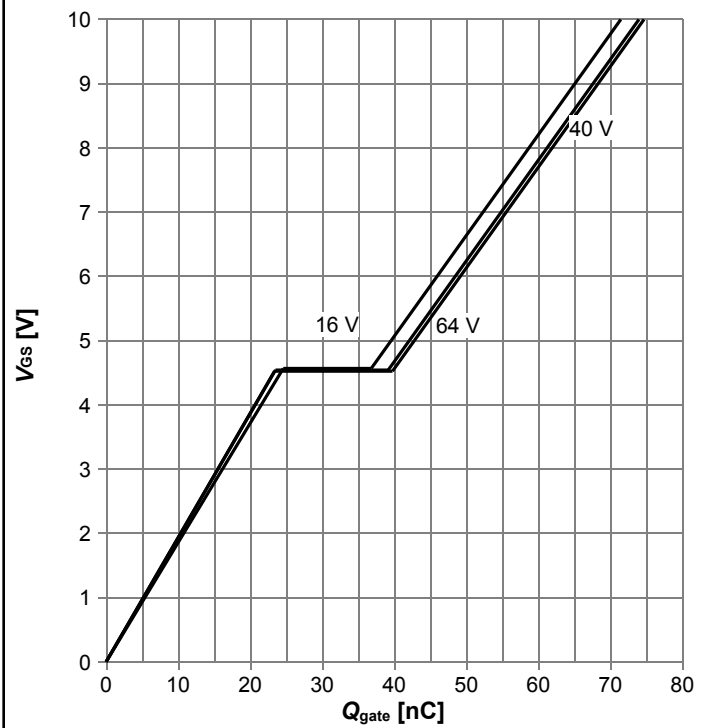


**Diagram 13: Avalanche characteristics**



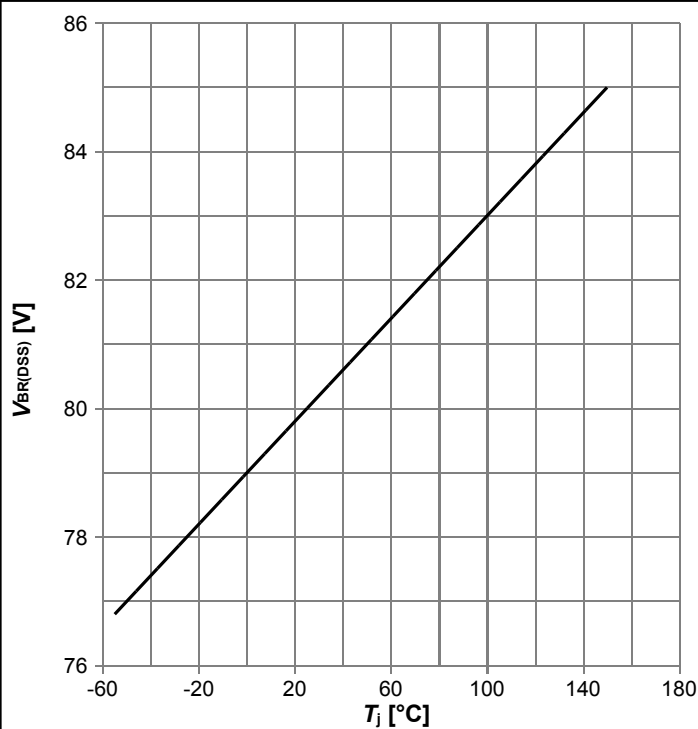
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

**Diagram 14: Typ. gate charge**



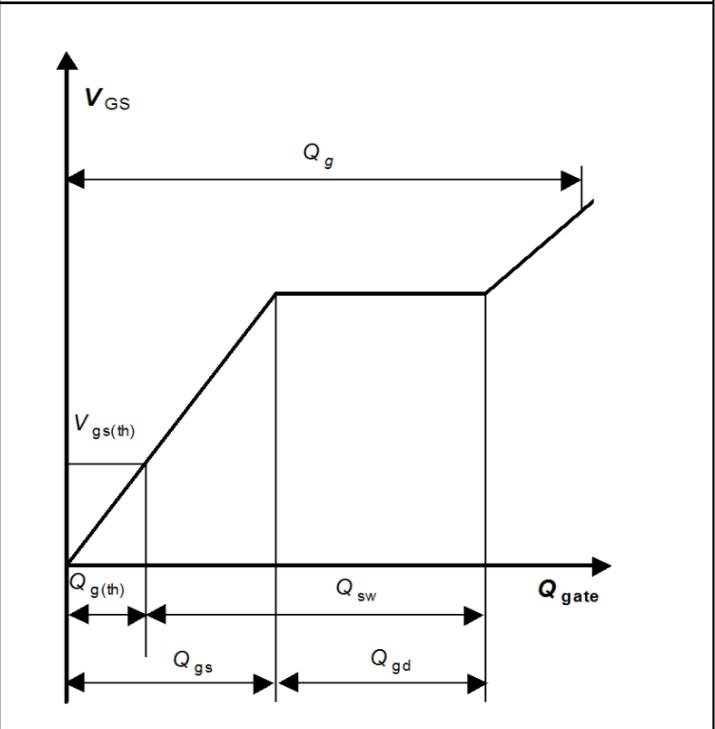
$V_{GS}=f(Q_{gate}); I_D=50 \text{ A pulsed}$ ; parameter:  $V_{DD}$

**Diagram 15: Drain-source breakdown voltage**

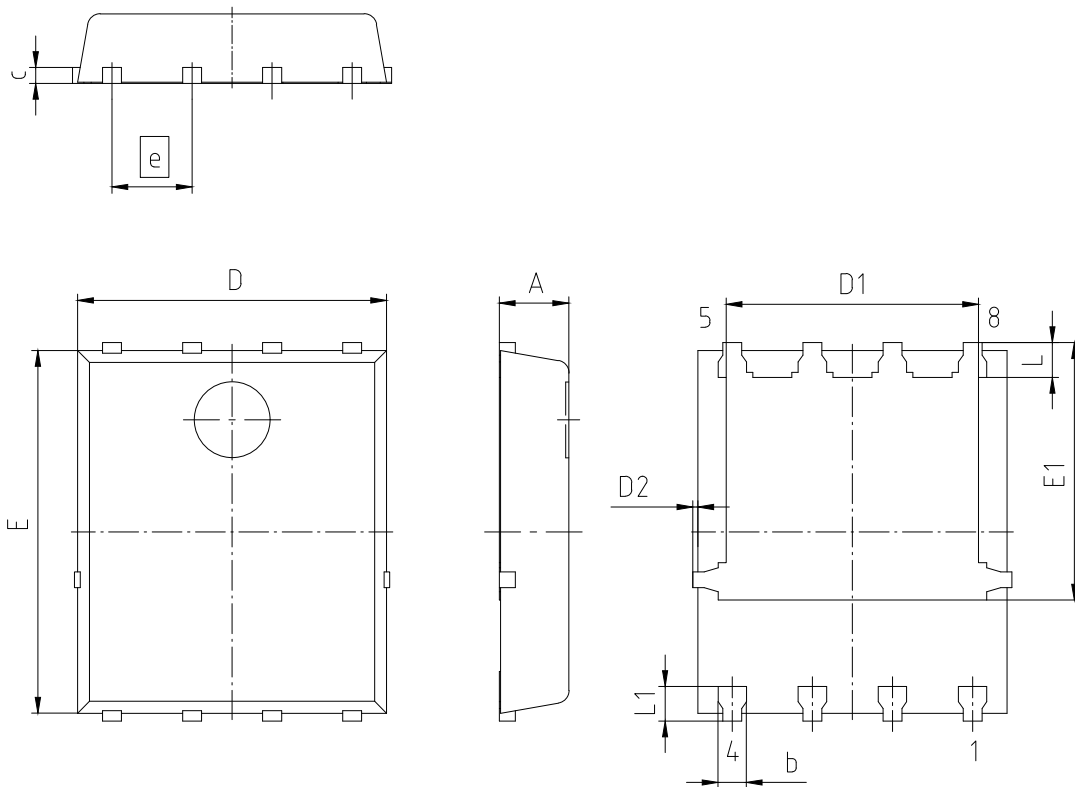


$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

**Diagram Gate charge waveforms**



## 5 Package Outlines



PACKAGE - GROUP NUMBER: PG-TDSON-8-U08		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	0.90	1.20
b	0.34	0.54
c	0.15	0.35
D	4.80	5.35
D1	3.90	4.40
D2	0.00	0.22
E	5.70	6.10
E1	4.05	4.25
e	1.27	
L	0.45	0.65
L1	0.45	0.65

- 1) EXCLUDING MOLD FLASH
- 2) REMOVAL ON MOLD GATE  
INTRUSION 0.1 MM  
PROTRUSION 0.1 MM
- 3) ALL METAL SURFACES ARE PLATED,  
EXCEPT AREA OF CUT

Figure 1 Outline PG-TDSON-8, dimensions in mm

## Revision History

BSC026N08NS5

**Revision: 2022-09-23, Rev. 2.3**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2014-12-18	Release of final version
2.1	2015-08-31	Rev. 2.0
2.2	2021-07-20	Update current rating
2.3	2022-09-23	Update outline drawing and footnotes

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